



2SB709A (3CG709A)

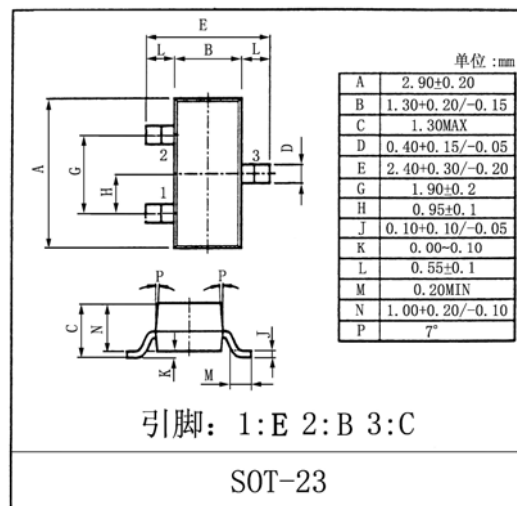
硅 PNP 半导体三极管/SILICON PNP TRANSISTOR

用途:用于普通功率放大/Purpose: General power amplifier applications.

特点:与 2SD601A(3DG601A) 互补/Features:Complementary pair with 2SD601A(3DG601A).

极限参数/Absolute maximum ratings(Ta=25°C)

| 参数符号 Symbol | 数值 Rating | 单位 Unit |
|------------------|--------------|------------|
| V _{CBO} | -45 | V |
| V _{CEO} | -45 | V |
| V _{EBO} | -7.0 | V |
| I _C | -100 | mA |
| I _{CP} | -200 | mA |
| P _C | 200 | mW |
| T _j | 150 | °C |
| T _{stg} | -55~150 | °C |



电性能参数/Electrical characteristics(Ta=25°C)

| 参数符号 Symbol | 测试条件 Test condition | | 数值 Rating | | | 单位 Unit |
|----------------------|------------------------|-----------------------|--------------|------------|------------|------------|
| | | | 最小值 Min | 典型值 Typ | 最大值 Max | |
| V _{CBO} | I _C =-10 μA | I _E =0 | -45 | | | V |
| V _{CEO} | I _C =-2mA | I _B =0 | -45 | | | V |
| V _{EBO} | I _E =-10 μA | I _C =0 | -7 | | | V |
| I _{CBO} | V _{CB} =-20V | I _E =0 | | | -0.1 | μA |
| I _{CEO} | V _{CE} =-10V | I _B =0 | | | -100 | μA |
| h _{FE} | V _{CE} =-10V | I _C =-2mA | 160 | | 460 | |
| V _{CE(sat)} | I _C =-100mA | I _B =-10mA | | -0.3 | -0.5 | V |
| f _T | V _{CB} =-10V | I _C =-1mA | f=200MHz | 80 | | MHz |
| C _{ob} | V _{CB} =-10V | I _E =0 | f=1MHz | 2.7 | | pF |

| | | | |
|---|---------|---------|---------|
| h _{FE} 分档 h _{FE} Classifications | Q | R | S |
| h _{FE} 范围 h _{FE} Range | 160-260 | 210-340 | 290-460 |
| 印章 Marking | H1BQ | H1BR | H1BS |



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